

# ADVANCED FULL ADDER DESIGN WITH 16NM TECHNOLOGY: HIGH-SPEED AND LOW-POWER IMPLEMENTATION USING MUX-BASED ARCHITECTURE

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## ABSTRACT-

This research proposes new circuits for XOR/XNOR and simultaneous XOR–XNOR functionality. The recommended circuits can run with very little power consumption and delays because to reduced output capacitance and short-circuit power dissipation. In addition, we propose six novel hybrid 1-bit full-adder (FA) circuits based on the state-of-the-art full-swing XOR–XNOR or XOR/XNOR gates. Each of the proposed circuits has advantages of its own in terms of speed, power consumption, power delay product (PDP), driving capabilities, and other characteristics. Comprehensive HSPICE and Cadence Virtuoso simulations are performed to evaluate the performance of the proposed designs. The simulation findings demonstrate that the proposed designs outperform competing FA solutions in terms of speed and power, based on Tanner, a 16-nm CMOS process technology model. A new method of sizing transistors is presented to optimize the PDP of the circuits. The suggested method minimizes the number of iterations needed to obtain the goal value for the optimal PDP by using a particle swarm optimization technique for numerical calculation. Regarding the recommended circuits, variations in the supply and threshold voltages, output capacitance, input noise immunity, and transistor size are investigated.

**Key words:** Swarm optimization, HSPICE

## I. INTRODUCTION

In today's world, now day's electronic systems plays a crucial role in day to day life. Digital Gadgets e.g., microprocessors, communication devices, and signal processors, are part of electronic systems. As the demand for electronic systems increases, the usage of circuits [1] are restricted to

consume low power and area consumption. Therefore, as there is growth in population and technology the demand for the portable devices such as mobile phones, tablets, and laptops have increased a lot , so the designers to meet the above

requirement designs the circuit which consumes low energy consumption and

area with the increase of speed. As the efficiency of many digital applications are to perform arithmetic operations, such as adder circuits, multipliers circuits and dividers schematics. As the technology is developed the chip density for the design of circuit is increased. So the plenty of transistors are doped into the singlechip.

## II. EXISTING METHOD

The Existing method XOR–XNOR circuit is saving almost 16.2%–85.8% in PDP, and it is 9%– 83.2% faster than the other circuits. The circuits of Fig. 1(d) and (e) have the very high delay due to its output feedback (which have the slow response problem). As can be seen in Table I, the efficiency of Fig. 1(e) is much worse and its delay is four times more than that of other circuits. Table I indicates that the structures have shown a better performance, which have the minimum NOT gates on the critical path and also have not feedback on the outputs to correct the output voltage level. To better evaluate the XOR–XNOR circuits, they are simulated at different power supply voltages from 0.6 to 1.5 V and also at different output loads from FO1 to FO16. The results of these two simulations are shown in Fig. 5(b) and (c). As seen in Fig. 5(b) and (c), the proposed XOR–XNOR circuit has the best performance in both simulations when compared with other structures.

The two input signal A, B are given to transistors. The signal B is given to P2 and signal A is given to P3. The signal B is given to N2 and P4 and the signal A is given to N2 and N3. The N3 is connected to P4. The signal B is given to N4 and P6 and the. Signal A is given to P5 and P6

The N4 is connected to N5. The signal B is given to N5 and the signal A is given to N6. The transistors P4 and N4 are shorted together and the out is Abar. The signal A is given to N9 and Ci is given to P9. The N2 and N3 transistors are shorted together and output is given N7 and Ci is given to N7, Ci is given to P7. The N2 and N3 transistors are shorted together and output is given N7 and N8. The P5 and P6 transistors are shorted together and output is given P7 and P8 Ci is given to N8, P8. The output to N2 and N3 is given to N9 and P9 and output of P5 and P6 is given to N10 and P10. The signal Ci and B is given to N10 and P10. The output of N7 and P7 and output of N8 and P8 are shorted together and the output is sum. The output of N9, P9 and N10, P10 are sorted together and output is carry. The circuit is simulated in 65nm technology and result are obtained.

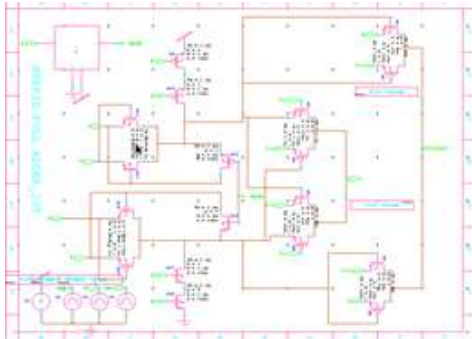


Figure 1: Schematic Of Hybrid Full Adder-20 Transistor

The above figure shows the schematic of hybrid full adder -20 transistors which is combinations of number of PMOS and NMOS logic is designed in 65nm technology .It is designed with tannerS-EDIT Tool.

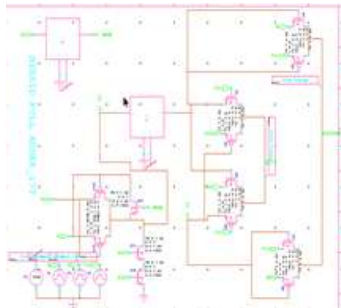


Figure 2: Simulation Of Hybrid Full Adder-20 Transistor

the above figure shows the PDP analysis of Hybrid Full Adder-20 Transistor. It analyzed by using tanner tool. The PDP is 340.98.For above simulation have done with 0.8 VDD.

The signal A,B are given to P4,P3.The transistor P4 is connected P5.The signal B is given to N3 and P5.The signal A is given to N3 and

N4.The signal A is given to P6 and P7 .The signal B is given P7 and N5.The transistor N5 is connected N6.The signal B is connected N6 and the signal A is connected to N7.The output of P5 and N5 is Abar.The output of N3 and N4 is given N8 , P9,N10 and P11.The output of P6 and P7 is given to P10,N11,P8 and N9.The signal Abar is given to p8 and n8.The signal Ci is given P9 and N9.

The signal Cibar is given N10 and P10.The signal Cibar is given N11 and P11.The output of N9,P9 and N10,P10 are shorted together and is given to inverter which consist of P12 and N12 ,the output of inverter is sum. The output of N8,P8 and N11,P11 are shorted together and is given to inverter which consist of N13 and P13 ,the output inverter is carry. The circuit is simulated in 65nm technology and result are obtained.

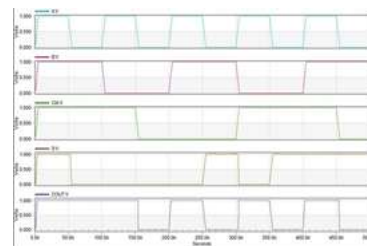


Figure 3: Simulation of Hybrid Full Adder-17 Transistor

The above figure shows the schematic of hybrid full adder 17 T transistors which is combinations of number of PMOS and NMOS logic is

designed in 16 nm technology .It is designed with tanner S-EDIT Tool.

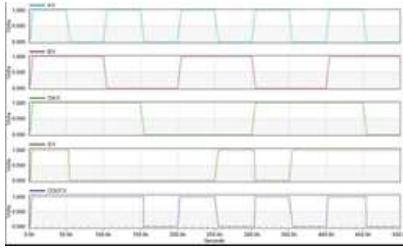


Figure 4: Simulation of Hybrid Full Adder17 T Transistor

The above figure shows the simulation results of Hybrid Full Adder17 T Transistor. It is simulated using CMOS Tanner-SPICE (Simulation Program with Integrated Circuit Emphasis) Tool. Wave forms are analyzed using W-EDIT(wave form editor).

The above figure shows the PDP analysis of Hybrid Full Adder17 T Transistor. It analyzed by using tanner tool. The PDP is 291.1505 .For above simulation have done with 5 VDD.

The signal A,B are given to P4,P3.The transistor P4 is connected P5.The signal B is given to N3 and P5.The signal A is given to N3 and N4.The signal A is given to P6 and P7 .The signal B is given P7 and N5.The transistor N5 is connected N6.The signal B is connected N6 and the signal A is connected to N7.The output of P5 and N5 is Abar .The output of N3 and N4 is given N8 , P9,N10 and P11.The output of P6 and P7 is given to P10,N11,P8 and N9.The signal Abar

is given to inverter which consist of P12 and N12.

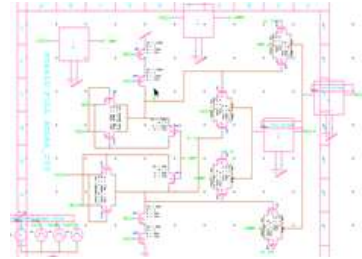


Figure 5: Schematic Of Hybrid Full Adder -B-26Transistor

The above figure shows the schematic of hybrid full adder -B-26 transistors which is combinations of number of PMOS and NMOS logic is designed in 65nm technology .It is designed with tanner S-EDIT Tool. The above figure shows the simulation results of Hybrid Full Adder-B-26Transistor.It is simulated using CMOS Tanner-SPICE (Simulation Program with Integrated Circuit Emphasis) Tool. Wave forms are analyzed using W-EDIT(wave form editor).

The signal A,B are given to P4,P3.The transistor P4 is connected P5.The signal B is given to N3 and P5.The signal A is given to N3 and N4.The signal A is given to P6 and P7 .The signal B is given P7 and N5.The transistor N5 is connected N6.The signal B is connected N6 and the signal A is connected to N7.The output of P5 and N5 is Abar.The output of N3 and N4 is given N8 , P9,N10 and P11.The output of

P6 and P7 is given to P10,N11,P8 and N9.The signal Abar is given to inverter which consist of P12 and N12.

The signal A,B are given to P4,P3.The transistor P4 is connected P5.The signal B is given to N3 and P5.The signal A is given to N3 and N4.The signal A is given to P6 and P7 .The signal B is given P7 and N5.The transistor N5 is connected N6.The signal B is connected N6 [2]and the signal A is connected to N7.The output of P5 and N5 is Abar.The output of N3 and N4 is given N8 , P9,N10 and P11.The output of P6 and P7 is given to P10,N11,P8 and N9.The signal Abar is given to p8 and n8.The signal Ci is given P9 and N9.

The signal Cibar is given N10 and P10.The signal Cibar is given N11 and P11.The output of N9,P9and N10,P10 are shorted together and is given to inverter which consist of P12 and N12 ,the output of inverter is sum. The output of N8,P8 and N11,P11 are shorted together and is given to inverter which consist of N13 and P13 ,the output inverter is carry. The circuit is simulated in

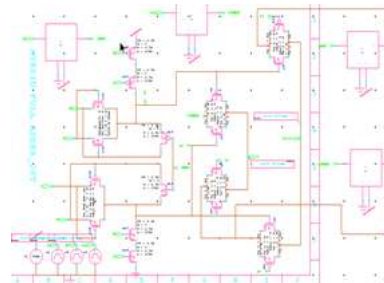


Figure 6: Schematic of Hybrid Full Adder HFA-NB-26T.

The above figure shows the schematic of hybrid full adder -B-26 transistors [3]which is combinations of number of PMOS and NMOS logic is designed in 65nm technology .It is designed with tanner S-EDIT Tool

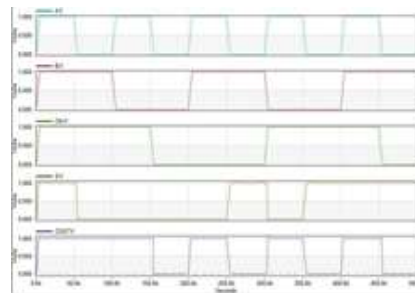


Figure 7: Simulation of Hybrid Full Adder-B-26 Transistor.

The above figure shows the simulation results of Hybrid Full Adder-B-26Transistor.It is simulated using CMOS Tanner-SPICE (Simulation Program with Integrated Circuit Emphasis) Tool. Wave forms are analyzed using W-EDIT(wave form editor). The signal A,B are given to P4,P3.The transistor P4 is connected



P5. The signal B is given to N3 and P5. The signal A is given to N3 and N4. The signal A is given to P6 and P7. The signal B is given P7 and N5. The transistor N5 is connected N6. The signal B is connected N6 and the signal A is connected to N7. The output of P5 and N5 is Abar. The output of N3 and N4 is given N8, P9, N10 and P11. The output of P6 and P7 is given to P10, N11, P8 and N9. The signal Abar is given to inverter which consist of P12 and N12.

The signal A, B are given to P4, P3. The transistor P4 is connected P5. The signal B is given to N3 and P5. The signal A is given to N3 and N4. The signal A is given to P6 and P7 [4]. The signal B is given P7 and N5. The transistor N5 is connected N6. The signal B is connected N6 and the signal A is connected to N7. The output of P5 and N5 is Abar. The output of N3 and N4 is given N8, P9, N10 and P11. The output of P6 and P7 is given to P10, N11, P8 and N9. The signal B is given to P8. The signal A is given to N8. The signal Ci bar is given P9 and N9. The

Signal Ci is given N10 and P10. The signal Ci is given N11 and P11. The output of N9, P9 and N10, P10 are shorted together and the output is sum. The output of N8, P8.

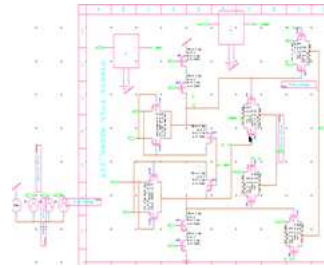


Figure 8: Simulation of Hybrid Full Adder HFA-22T

The above figure shows the schematic of hybrid full adder -22 transistors which is combinations of number of PMOS and NMOS logic is designed in 65nm technology. It is designed with tannerS-EDIT Tool.

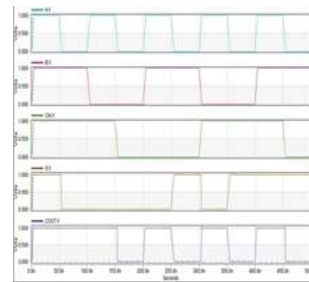


Figure 9: Simulation of Hybrid Full Adder-22 Transistor

The above figure shows the simulation results of Hybrid Full Adder-22 Transistor. It is simulated using CMOS Tanner-SPICE (Simulation Program with Integrated Circuit Emphasis) Tool. Wave forms are analyzed using W-EDIT (wave form editor).

The input signal A is given to inverter which consists of P1 and N1

transistors. Carry signal  $C_i$  is given to inverter which consists of P2 and N2 transistor[5]. The signal A is given to P3,P2 and signal B is given P2,N4.The output of P3,P2 are shorted together and is given to N4,the N4 is connected to N3.The signal A is given to N3 and signal B is given to N2.The output of P3,P2 is given to inverter which consists of P4 and N5.The output of inverter is given to N6,N7,N8,P7.

The signal  $C_i$  is given to N6,P5,N7,P6,N9,P7.The input of inverter is given P6 ,P5,N9andP8.The output of transistors N6,P5 and N7,P6 are shorted together .The output is sum. The output of N8, N7 and N9, P8are shorted together and the output is carry. The circuit is simulated in 65nm technology and result are obtained.

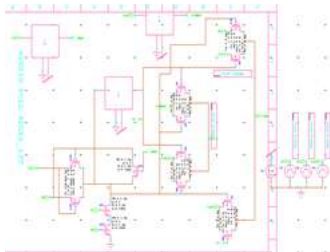


Figure 10: Simulation of Hybrid Full Adder HFA- 19T

The above figure shows the schematic of hybrid full adder -19 transistors which is combinations of number of PMOS and NMOS logic is designed in 65nm technology .It is designed with tanner S-EDIT Tool.

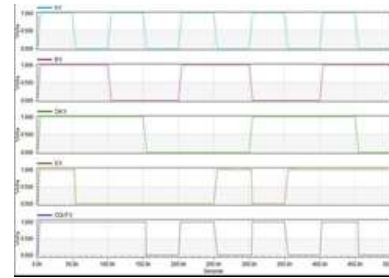


Figure 11: Simulation of Hybrid Full Adder-19 Transistor

The above figure shows the simulation results of Hybrid Full Adder-17 Transistor. It is simulated using CMOS Tanner-SPICE[6] (Simulation Program with Integrated Circuit Emphasis) Tool. Wave forms are analyzed using W-EDIT(wave form editor).

### III. PROPOSED METHOD

For computational arithmetic, a full adder is the primary logic units in VLSI applications. A new full adder circuit design has been presented in this article which is based on input switching activity pattern and gate diffusion input (GDI) technique.[7] The adder has been designed in two stages. The first stage is an XOR–XNOR module, whereas, the final stage is for the required outputs. By using the switching activity pattern of inputs and GDI techniques at each stage, the switching activities of the transistors have been minimized. This improves

delay, power consumption and computational complexity. The adder has been designed and evaluated by using the synopsis tool and compared with different existing adder cells found in the literature. It is found that the presented adder shows an improvement at least 72.86% and 66.67% in terms of speed and energy consumption, respectively. Extensive performance analyses of the full adder have also been evaluated at 16 nm technology node which shows promising performances in both the technology nodes. Summarily, the main contributions of the proposed work are listed below:

1. A 1-bit full adder circuit has been designed for VLSI applications based on switching activity and GDI technique which is compatible both with CMOS and CNFET technology.
2. The circuit has been designed in two stages. In the first stage, an XOR–XNOR [8] module has been designed, whereas, in the second stage
3. the sum and carry modules have been designed. The overall circuit requires only 10 transistors.
4. By utilizing the switching activity pattern of the inputs and GDI techniques at each stage, the switching activities of the transistor (transitions) have been minimized during data flow from inputs to the outputs which ensures less delay and low power

consumption.

5. Moreover, as  $C_{in}$  is introduced at the final stage, the initial circuit operation becomes independent of  $C_{in}$  that helps in further reduction in delay.
6. The simulations and analysis have been carried out in 90 nm CMOS, 32 nm CMOS and 32 nm technology nodes.
7. A comparative analysis has been carried out comprehensively to establish the utility of the proposed design.

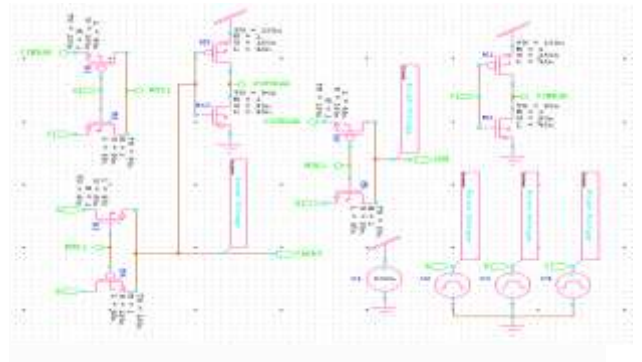


Figure 12: Simulation of Hybrid Full Adder-10 Transistor

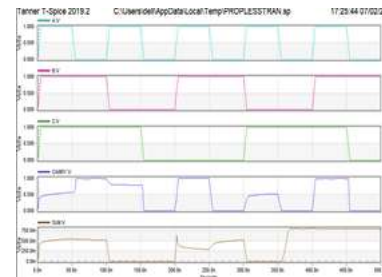


Figure 13: Simulation of Hybrid Full Adder-10 Transistor



The above figure shows the simulation results of Hybrid Full Adder-17 Transistor. It is simulated using CMOS Tanner-SPICE (Simulation Program with Integrated Circuit Emphasis) Tool. Wave forms are analyzed using W-EDIT(wave form editor).

#### IV. CONCLUSION

In this research, we first evaluated XOR-XNOR schematics. The simulation illustrates the limitations of NOT gates and positive feedback in a circuit. The presence of feedback causes an increase in output capacitance, latency, and power consumption[9]. We then propose new XOR-XNOR schemes that may not suffer from the aforementioned problems. We used the recommended XOR-XNOR gates to develop three new FA circuits for various algorithms. Simulations of FA circuits with different configurations show that all of the recommended designs perform remarkably well. Simulation experiments show that the suggested FA schematics save PDP by up to 23% when compared to alternative FA[10] circuit designs. The quickest and most potent FA designs are those that are recommended.

#### A. FUTURE SCOPE

The need for low power architecture is a major challenge in high-performance digital systems, including microprocessors, digital signal processors (DSPs), and other applications. Because of the higher operating speed and chip density, high clock frequency chips are built with ever-increasing complexity. Low power design is also required in high-end systems with high integration densities in order to reduce power consumption and speed up operation.

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